

## Dual Line ESD Protection Diode Array

### UM5062 QFN3 1.4×1.1

#### General Description

The UM5062 ESD protection diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. It features large cross-sectional area junctions for conducting high transient currents, offers desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs.

The UM5062 ESD protection diode protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The UM5062 is available in a QFN3 1.4mm×1.1mm package with working voltages of 5 volt.

It gives designer the flexibility to protect one or two unidirectional line in applications where arrays are not practical. Additionally, it may be "sprinkled" around the board in applications where board space is at a premium. It may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (±15kV air, ±8kV contact discharge).

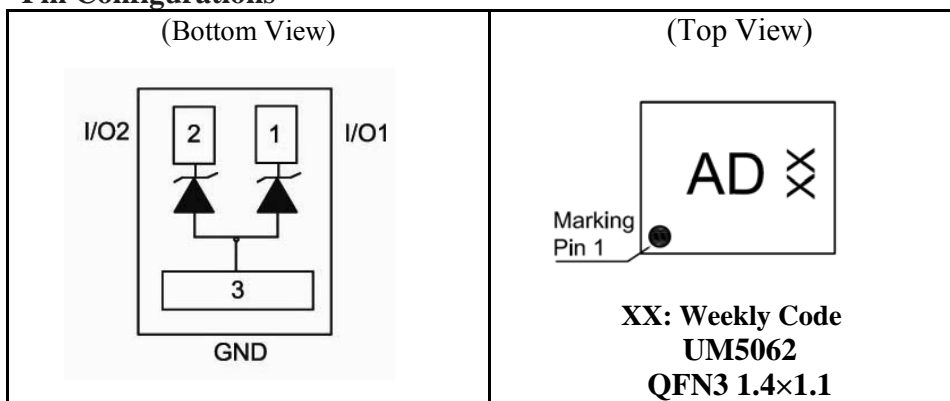
#### Applications

Cell Phone Handsets and Accessories  
 Microprocessor based equipment  
 Personal Digital Assistants (PDA's)  
 Notebooks, Desktops, and Servers  
 Portable Instrumentation  
 Cordless Phones  
 Digital Cameras  
 Peripherals  
 MP3 Players

#### Features

Transient protection for data & power lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact)  
 Small package for use in portable electronics  
 Suitable replacement for MLV's in ESD protection applications  
 Protect one or two I/O lines  
 Low clamping voltage  
 Stand off voltages: 5V  
 Low leakage current  
 Solid-state silicon-avalanche technology

#### Pin Configurations



## Ordering Information

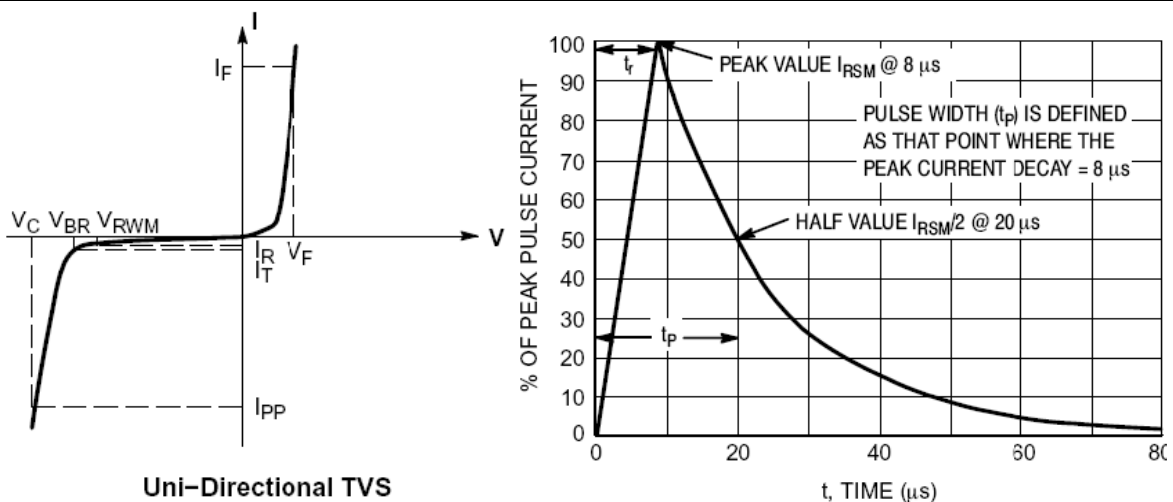
Part Number	Working Voltage	Packaging Type	Channel	Marking Code	Shipping Qty
UM5062	5.0V	QFN3 1.4×1.1	2	AD	3000/7 Inch Reel

## Absolute Maximum Ratings

RATING	SYMBOL	VALUE	UNITS
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PK}$	140	Watts
Maximum Peak Pulse Current ( $t = 8/20\mu s$ )	$I_{PP}$	11	Amps
Lead Soldering Temperature	$T_L$	260 (10 sec.)	$^{\circ}C$
Operating Temperature	$T_J$	-55 to +125	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}C$

## Symbol Definition

PARAMETER	SYMBOL
Maximum Reverse Peak Pulse Current	$I_{PP}$
Clamping Voltage @ $I_{PP}$	$V_C$
Working Peak Reverse Voltage	$V_{RWM}$
Maximum Reverse Leakage Current @ $V_{RWM}$	$I_R$
Breakdown Voltage @ $I_t$	$V_{BR}$
Test Current	$I_t$
Forward Current	$I_F$
Forward Voltage @ $I_F$	$V_F$
Peak Power Dissipation	$P_{PK}$
Max. Capacitance @ $V_R = 0V, f = 1MHz$	$C$



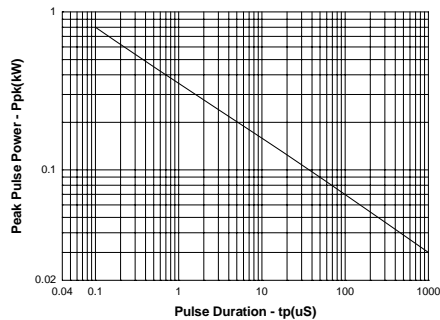
## Electrical Characteristics

(T=25°C, Device for 5.0V Reverse Stand-off Voltage)

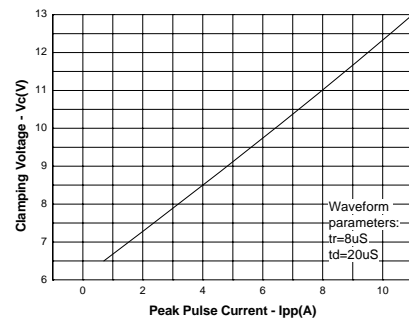
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Stand-Off Voltage	$V_{RWM}$				5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_t = 1mA$	6	6.8	7.2	V
Reverse Leakage Current	$I_R$	$V_{RWM} = 5V, T=25^\circ C$			0.1	$\mu A$
Clamping Voltage	$V_C$	$I_{PP} = 5A, t_p = 8/20\mu S$			9.1	V
		$I_{PP} = 11A, t_p = 8/20\mu S$			13	
Forward Voltage	$V_F$	$I_F = 10mA$		0.8		V
Junction Capacitance	$C_J$	$V_R = 0V, f = 1MHz$		40	55	pF
Junction Capacitance	$C_J$	$V_R = 2.5V, f = 1MHz$		30	40	pF

## Typical Operating Characteristics

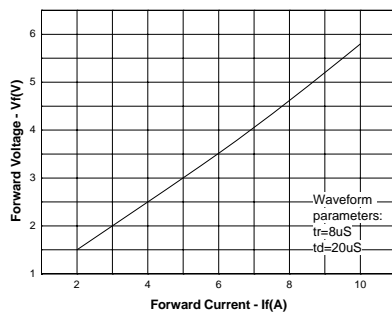
### Non-Repetitive Peak Pulse Power vs. Pulse Time



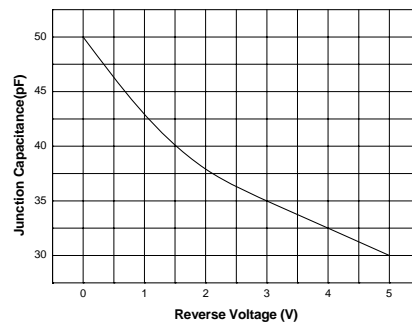
### Clamping Voltage vs. Peak Pulse Current



### Forward Voltage vs. Forward Current



### Junction Capacitance vs. Reverse Voltage



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## Applications Information

### Device Connection Options

UM5062 ESD protection diode is designed to protect one or two I/O lines. The device is unidirectional and may be used on lines where the signal polarity is above ground. The cathode band should be placed towards the line that is to be protected.

### Circuit Board Layout Recommendations for Suppression of ESD

Good circuit board layout is critical for the suppression of ESD induced transients. The following guidelines are recommended:

- Place the TVS near the input terminals or connectors to restrict transient coupling.
- Minimize the path length between the TVS and the protected line.
- Minimize all conductive loops including power and ground loops.
- The ESD transient return path to ground should be kept as short as possible.
- Never run critical signals near board edges.
- Use ground planes whenever possible. For multilayer printed-circuit boards, use ground vias.
- Keep parallel signal paths to a minimum.
- Avoid running protection conductors in parallel with unprotected conductor.
- Minimize all printed-circuit board conductive loops including power and ground loops.
- Avoid using shared transient return paths to a common ground point.

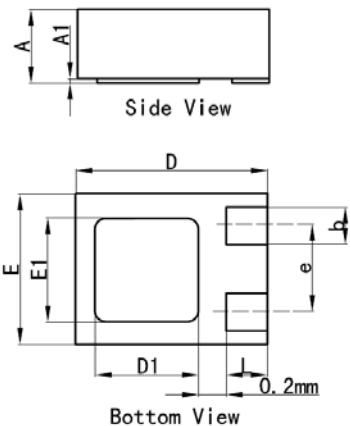
### Matte Tin Lead Finish

Matte tin has become the industry standard lead-free replacement for SnPb lead finishes. A matte tin finish is composed of 100% tin solder with large grains. Since the solder volume on the leads is small compared to the solder paste volume that is placed on the land pattern of the PCB, the reflow profile will be determined by the requirements of the solder paste. Therefore, these devices are compatible with both lead-free and SnPb assembly techniques. In addition, unlike other lead-free compositions, matte tin does not have any added alloys that can cause degradation of the solder joint.

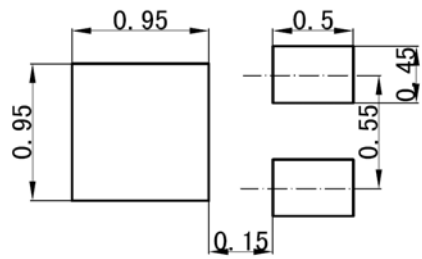
## Package Information

### UM5062 QFN3 1.4×1.1

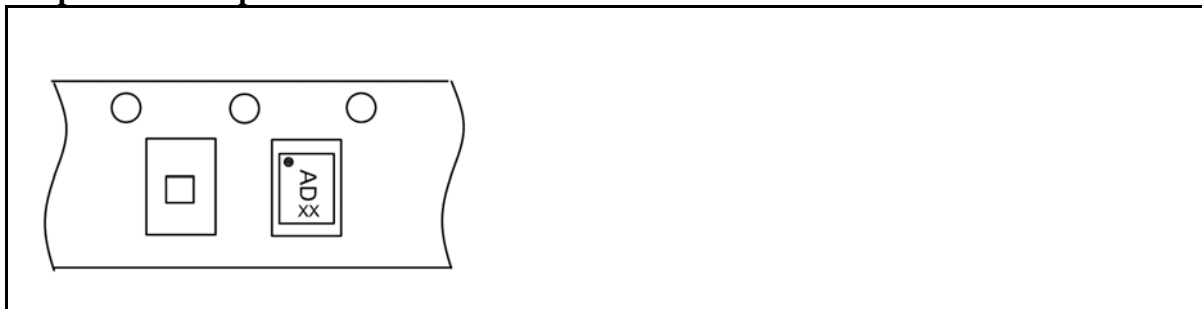
## Outline Drawing

	DIMENSIONS		
	MILLIMETERS		
Symbol	Min	Typ	Max
A	0.47	0.50	0.53
A1	0	0.02	0.05
D	1.35	1.40	1.475
E	1.05	1.10	1.175
D1	0.65	0.75	0.85
E1	0.65	0.75	0.85
b	0.25	0.30	0.35
L	0.225	0.275	0.325
e		0.55	

## Land Pattern

	<p>NOTES:</p> <ol style="list-style-type: none"> <li>Compound dimension: 1.40×1.10;</li> <li>Unit: mm;</li> <li>General tolerance±0.05mm unless otherwise specified;</li> <li>The layout is just for reference.</li> </ol>
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## Tape and Reel Specification



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